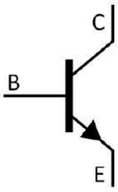
Silicon NPN transistor in a SOT-323 Plastic Package.

High h_{FE} and V_{CEO}



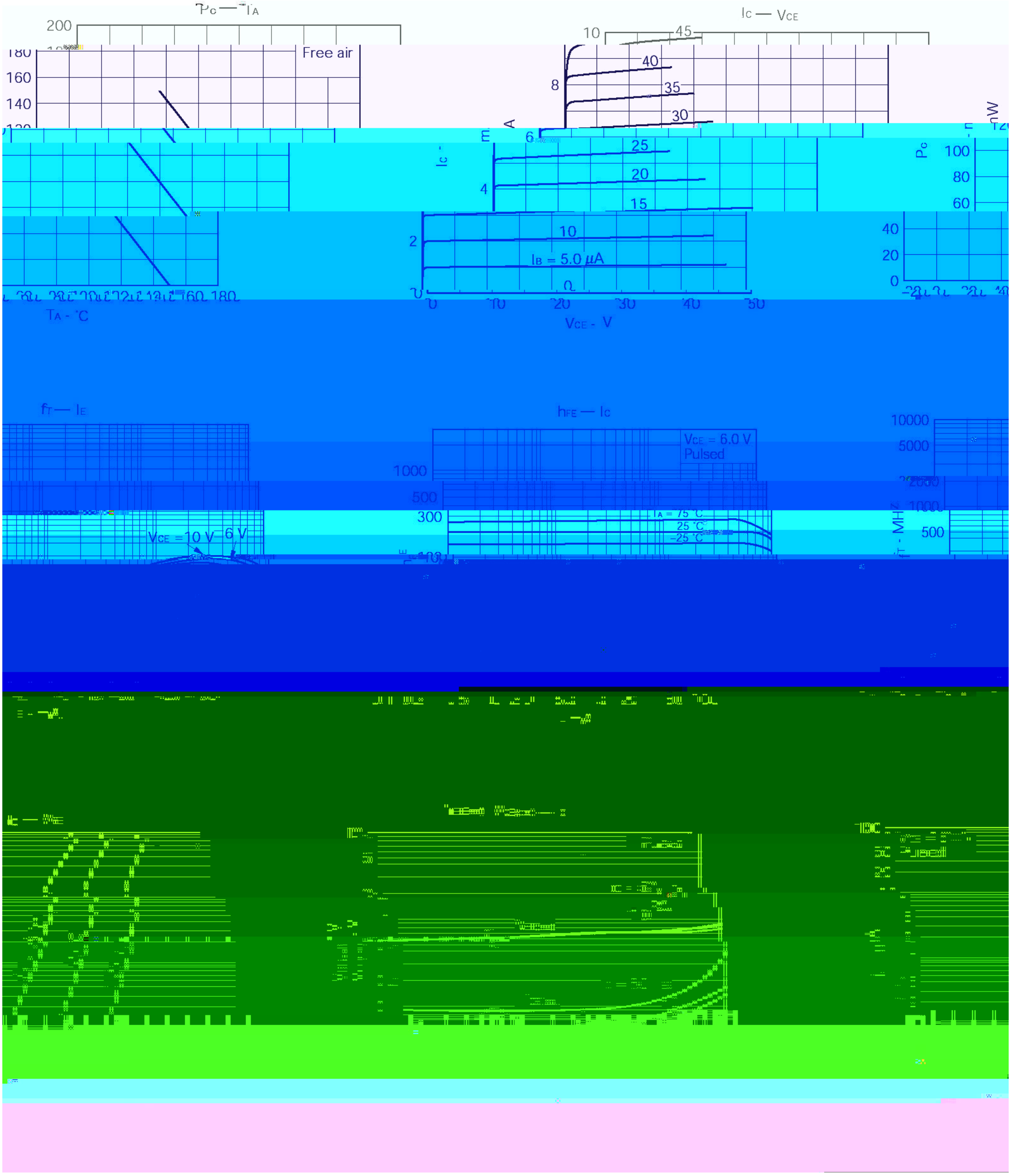
/ Absolute Maximum Ratings(Ta=25)

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	60	V
Collector to Emitter Voltage	V_{CEO}	50	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	100	mA
Collector Power Dissipation	P_C	150	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

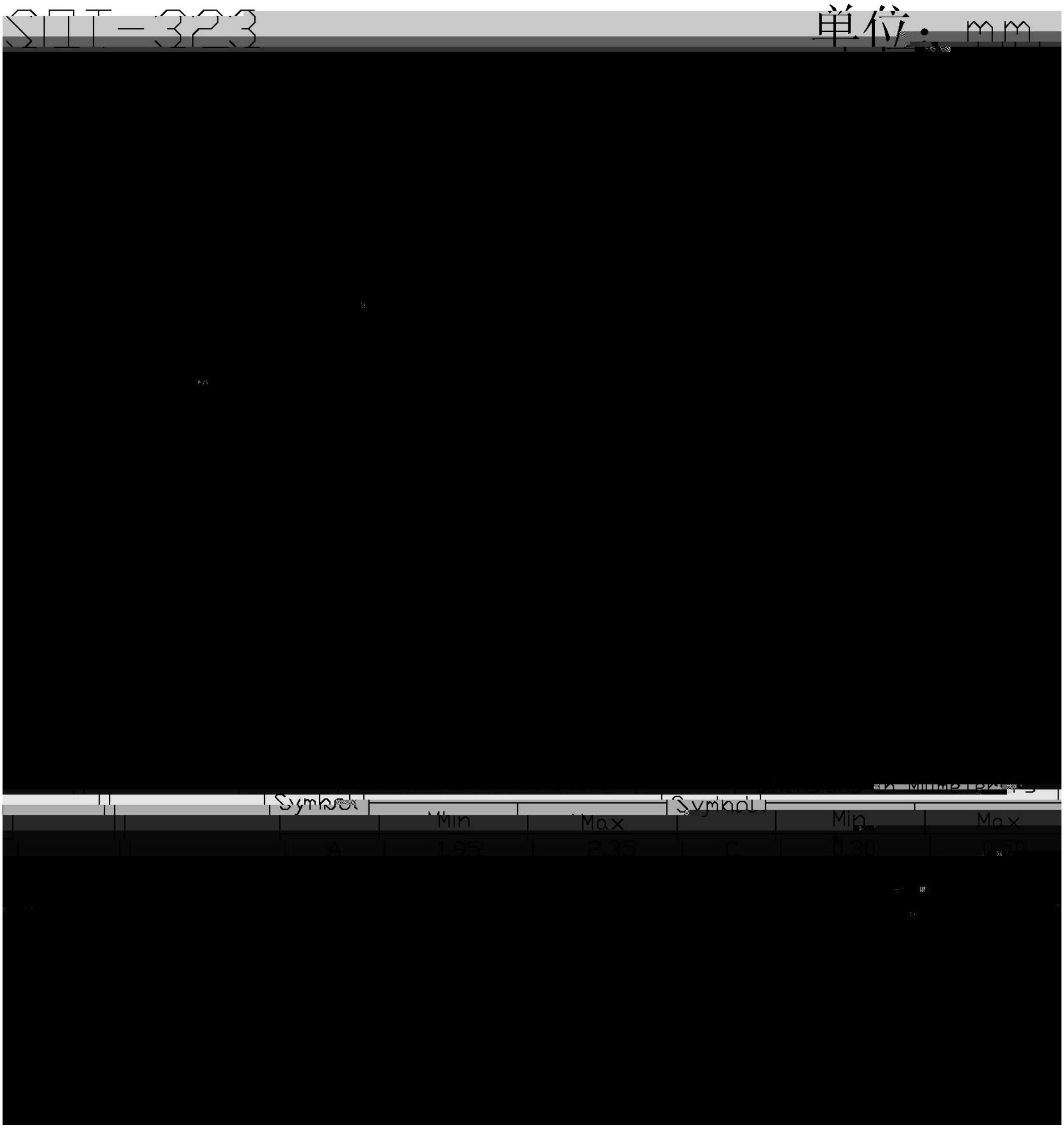
/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-Off Current	I_{CBO}	V_{CB}=60V I_E=0			0.1	μA
Emitter Base Cut-Off Current	I_{EBO}	V_{EB}=5.0V I_C=0			0.1	μA
DC Current Gain	h_{FE}	V_{CE}=6.0V I_C=1.0mA	90	200	600	
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=100mA I_B=10mA		0.15	0.3	V
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	I_C=100mA I_B=10mA		0.86	1.0	V
Base to Emitter Voltage	V_{BE}	V_{CE}=6.0V I_C=1.0mA	0.55	0.62	0.65	V
Transition Frequency	f_T	V_{CE}=6.0V I_C=10mA		250		MHz
Collector Output Capacitance	C_{ob}	V_{CB}=6.0V I_E=0 f=1.0MHz		3.0		pF

/ Electrical Characteristic Curve



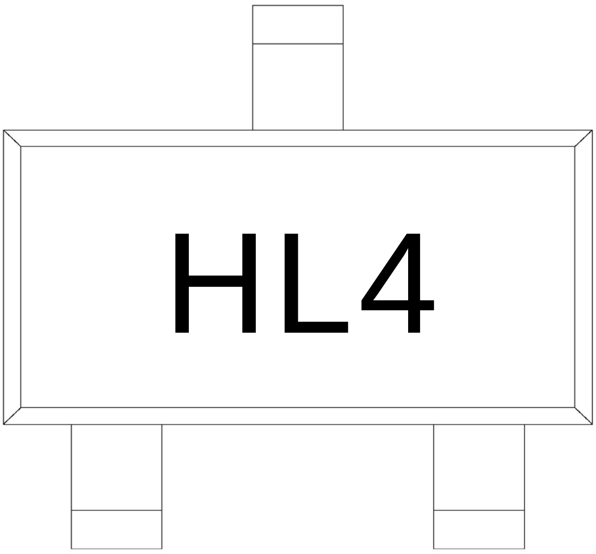
/ Package Dimensions



SOT-323　单位：mm

Symbol	Min	Max	Symbol	Min	Max
A	1.95	2.35	C	0.30	0.50

/ Marking Instructions



H

L4

Note:

H: Company Code.

L4: Product Type.

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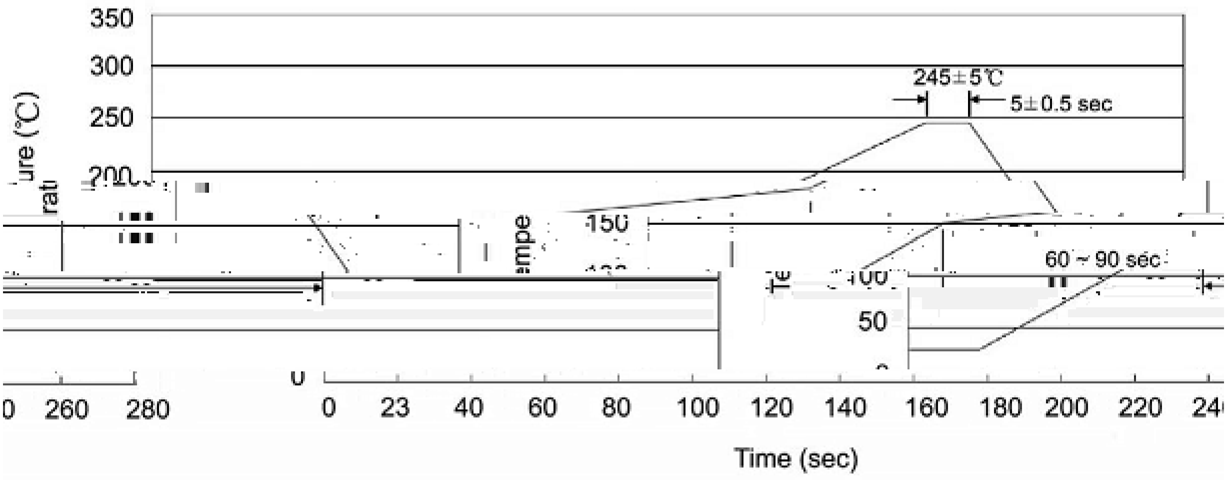

Note:

1 25 150 60 90sec;

2 245 5 5 0.5sec;

3 2 10 /sec.

1.Preheating:25~150 , Time:60~90sec.

2.Peak Temp.:245 5 , Duration:5 0.5sec.

3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

260 5 10 1 sec.

Temp.:260±5 Time:10±1 sec

/ Packaging SPEC.

/ REEL

Package Type	Units					Dimension (unit mm³)		
	Units/Reel /	Reels/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Reel	Inner Box	Outer Box
SOT-323	3,000	10	30,000	6	180,000	7 ×8	180×120×180	390×385×205

/ Notices